Abstracts

Millimeter IMPATT Sources for the 130-170-GHz Range

K.P. Weller, R.S. Ying and D.H. Lee. "Millimeter IMPATT Sources for the 130-170-GHz Range." 1976 Transactions on Microwave Theory and Techniques 24.11 (Nov. 1976 [T-MTT] (Special Issue on Millimeter Waves: Circuits, Components, and Systems)): 738-743.

Device and circuit design of silicon IMPATT sources in the 130-170-GHz range is discussed. A 170-GHz source has been developed with 16 mW at the isolator output having an AM double-side-band noise-to-signal ratio of -115 dB per 1 kHz beyond 70 kHz from carrier.

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